

Gain, SNR and Risetime of the “Penn I” Amplifier

SNW, July 25, 2017

(some early results on HFS data taken within the “PICOSEC” project at SPS July5-18)

The signal from the HFS Silicon detector was calibrated using a 5.4 KeV X - Ray source and then compared to the signal seen at the same operating voltage (1800 V) and with the same front end electronics (see SNW note Feb. 21, 2017

http://physics.princeton.edu/~mcdonald/LHC/White/white_resnati_170222.pdf).

From this comparison we find that The most probable signal from a 150 GeV muon (MIP) is 5,380 e-h pairs

To find the input charge into the amplifier we use an (average) Gain curve from similar devices.

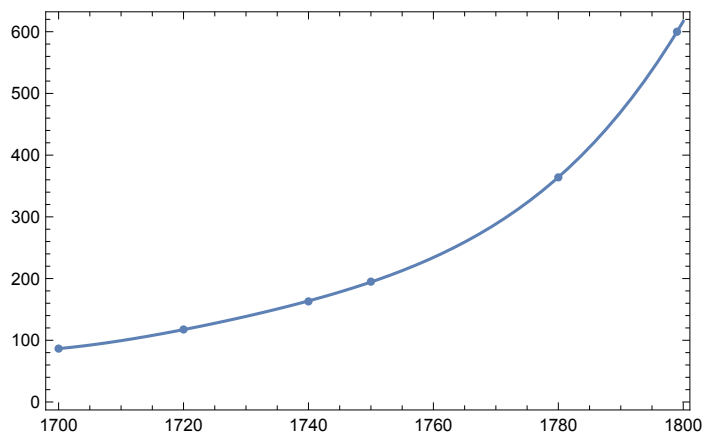
The nominal Detector capacitance for the RMD “8x8” diode is 0.79 pF/mm² and since the detector active area is ~9x9 we take this to ~60 pF. However the effective capacitance is lower in the “mesh readout” capacitive coupling scheme. We estimate $C_D \sim 25$ pF.

```
Gain = {{1700, 86.5}, {1720, 117.5},  
        {1740, 163}, {1750, 195}, {1780, 364}, {1799, 600}}  
  
{{1700, 86.5}, {1720, 117.5}, {1740, 163}, {1750, 195}, {1780, 364}, {1799, 600}}
```

```
lm = LinearModelFit[Gain, {x, x^2, x^3, x^4}, x]
```

```
FittedModel[ $6.32833 \times 10^7 - 146774. x + 127.668 x^2 - 0.0493609 x^3 + 7.15763 \times 10^{-6} x^4$ ]
```

```
Show[ListPlot[Gain], Plot[lm[x], {x, 1700, 1800}], Frame → True]
```



The Penn1 Detector/Amp was operated with bias voltages of 1700, 1726, 1751, 1772 in the July '17 testbeam.

```
HV = {1700, 1726, 1751, 1772};
```

```
lm[HV[[4]]]
```

```
301.563
```

```
qmip = 5380 * 1.6 * 10-19 * 1012
```

```
{0.0008608}
```

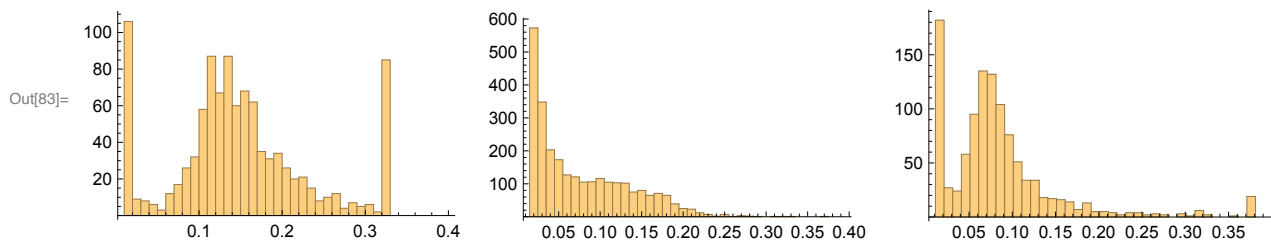
Signal charge vs Silicon Bias Voltage (in femtoCoulombs)

```
qin = Table[qmip * lm[HV[[i]]], {i, 4}]
```

```
{{0.074497}, {0.111649}, {0.170318}, {0.259585}}
```

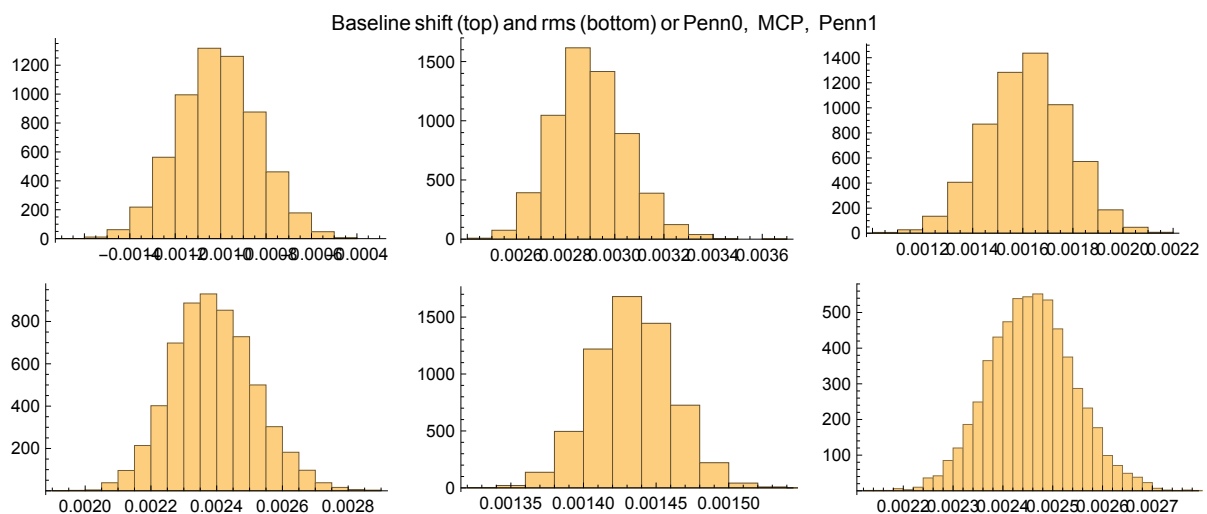
Correction of Scope Signal to Penn Amp output : Since we use a second stage of 13 dB we need to divide by ~4.5 to get the correct scale of mV/fCoulomb.

Peak (Volts) for Penn0 (1798 V), MCP, Penn1 (1772 V)



Referring to the above figure, PennI for an input charge of 0.26 fCoulombs produces an output of 70 mV/(4.5).

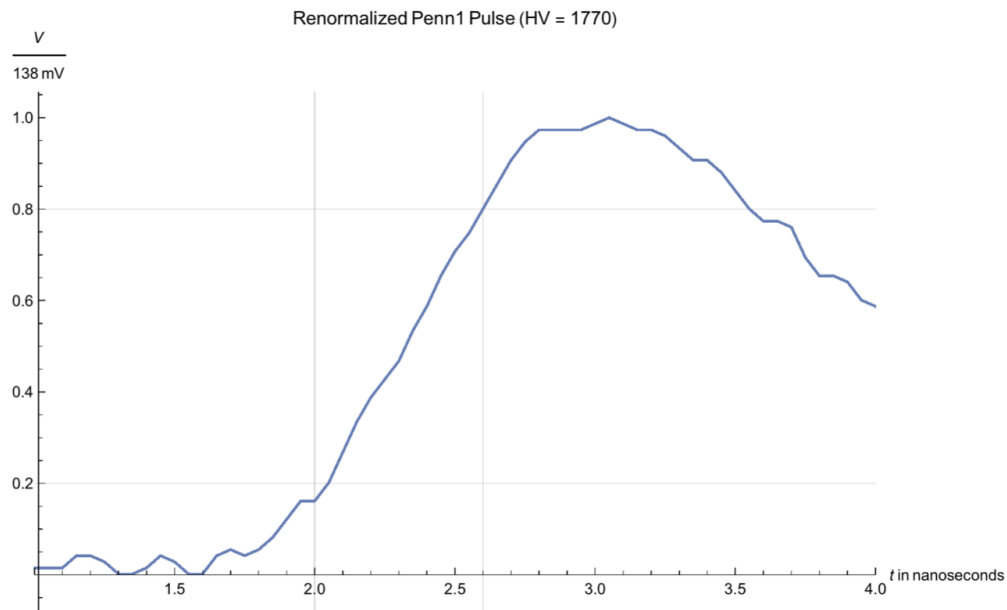
= > 60 mV per femtoCoulomb. By comparison the rms noise (at full 4 GHz bandwidth is 2.5mV/4.5~600 microVolts. See below:



More beam analysis in progress but we typically have 10 - 100 k events per run and the triggers were from a large area scintillator (2 x3cm²) and

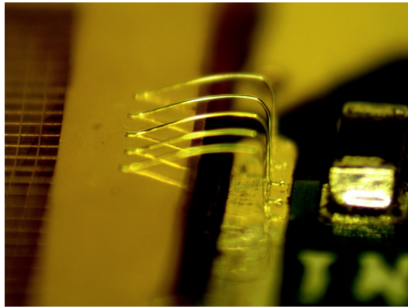
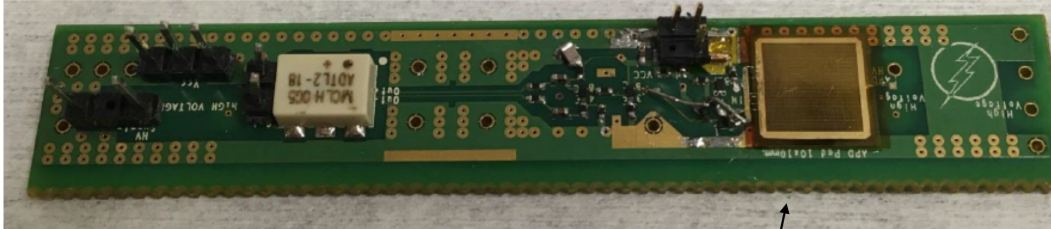
recorded with a fast MCP - hence the poor separation of MIP from noise in the above raw plots.

So timing characteristics will follow but a peek at a typical waveform below shows major improvement in signal risetimes from the $\sim 1.2 - 1.4$ nsec we were used to.



Below are figures of the new construction techniques that led to good performance of Penn I.

New Package



8x8mm² Silicon Sensor
capacitive readout
woven MMegas mesh
replaced by eForm Ni

wire bond to input transistor